**Product data sheet** 

## 1. General description

Hyperfast power diode in a 2-lead TO247 plastic package.

### 2. Features and benefits

- Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- · Low leakage current
- · Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by Epoxy Mold Compound

## 3. Applications

- UPS
- EV Charger
- · Welding Machine
- Air Conditioner

### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter                           | Conditions   | Notes |     | Values |      | Unit |
|------------------|-------------------------------------|--|-------|-----|--------|------|------|
| Absolute         | maximum rating                      |  |       |     |        |      |      |
| $V_{RRM}$        | repetitive peak reverse voltage     |  |       |     | 650    |      | V    |
| $I_{F(AV)}$      | average forward current             | $δ = 0.5$ ; square-wave pulse; $T_{mb} \le 115$ °C;<br>Fig. 1; Fig. 2; Fig. 3                                      |       | 50  |        |      | А    |
| I <sub>FRM</sub> | repetitive peak forward current     | $\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse                               |       | 100 |        |      | А    |
| I <sub>FSM</sub> | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;<br>Fig. 4   |       | 460 |        | Α    |      |
|                  |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse   |       | 506 |        |      | А    |
| Symbol           | Parameter                           | Conditions   | Notes | Min | Тур    | Max  | Unit |
| Static ch        | aracteristics                       |  |       |     |        |      |      |
| $V_{F}$          | forward voltage                     | I <sub>F</sub> = 50 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |       | -   | 1.50   | 2.00 | V    |
|                  |                                     | I <sub>F</sub> = 50 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |       | -   | 1.23   | 1.60 | V    |
| Dynamic          | characteristics                     |  |       |     | 1      |      |      |
| t <sub>rr</sub>  | reverse recovery time               | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |       | -   | 40     | -    | ns   |

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description                        | Simplified outline | Graphic symbol     |
|-----|--------|------------------------------------|--------------------|--------------------|
| 1   | K      | cathode                            |                    | K <b>— K</b> — A   |
| 2   | А      | anode                              |                    | K — A<br>001aaa020 |
| mb  | mb     | mounting base; connected to cathod | K A TO247-2L       |                    |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number    | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|----------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| BYC50MW-650PT2 | TO247-2L     | BYC50MW-650PT2Q       | Tube           | 30                     | TO247L-2L       | 10-Nov-2020        |

## 7. Marking

#### Table 4. Marking codes

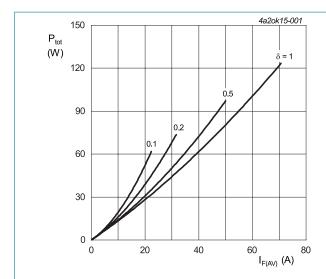
| Type number    | Marking codes     |
|----------------|-------------------|
| BYC50MW-650PT2 | BYC50MW<br>650PT2 |

## 8. Limiting values

### Table 5. Limiting values

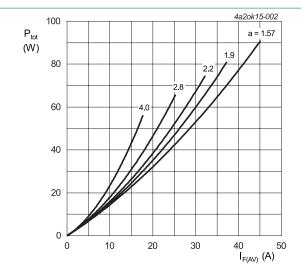
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions   | Notes | Values     | Unit |
|--------------------|-------------------------------------|--|-------|------------|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |  |       | 650        | V    |
| $V_{RWM}$          | crest working reverse voltage       |  |       | 650        | V    |
| $V_R$              | reverse voltage                     | DC   |       | 650        | V    |
| I <sub>F(AV)</sub> | average forward current             | $δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C;<br>Fig. 1; Fig. 2; Fig. 3         |       | 50         | A    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 115 °C; square-wave pulse |       | 100        | Α    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4                        |       | 460        | Α    |
|                    |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                               |       | 506        | А    |
| T <sub>stg</sub>   | storage temperature                 |  |       | -65 to 175 | °C   |
| T <sub>j</sub>     | junction temperature                |  |       | -65 to 175 | °C   |



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V<sub>o</sub> = 1.274 V; R<sub>s</sub> = 0.0067 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.274 V;  $R_s$  = 0.0067  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

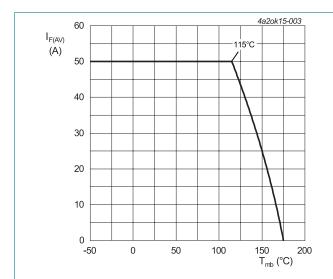


Fig. 3. Forward current as a function of mounting base temperature; maximum values

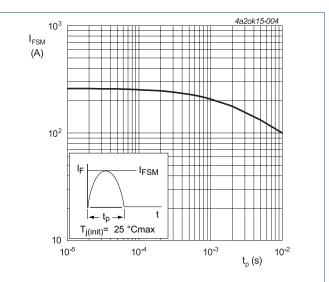


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions    | Notes | Min | Тур | Max  | Unit |
|-----------------------|--|---------------|-------|-----|-----|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base    | <u>Fig. 5</u> |       | -   | -   | 0.62 | K/W  |
| $R_{\text{th(j-a)}}$  | thermal resistance<br>from junction to<br>ambient free air | in free air   |       | -   | 40  | -    | K/W  |

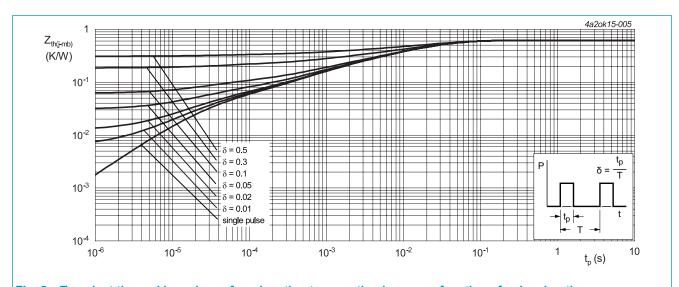
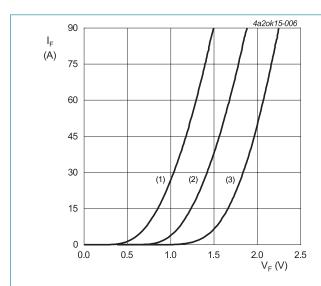


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

| Symbol          | Parameter                       | Conditions   | Notes | Min | Тур  | Max  | Unit |
|-----------------|---------------------------------|--|-------|-----|------|------|------|
| Static ch       | aracteristics                   |  |       |     |      |      |      |
| $V_{F}$         | forward voltage                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>   |       | -   | 1.50 | 2.00 | V    |
|                 |                                 | I <sub>F</sub> = 50 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>  |       | -   | 1.23 | 1.60 | V    |
| I <sub>R</sub>  | reverse current                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C   |       | -   | 0.5  | 30   | μA   |
|                 |                                 | V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C  |       | -   | 0.2  | 2    | mA   |
| Dynamic         | characteristics                 |  |       |     |      |      |      |
| Q <sub>r</sub>  | reverse charge                  | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$   |       | -   | 440  | -    | nC   |
|                 |                                 | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$  |       | -   | 1650 | -    | nC   |
| t <sub>rr</sub> | reverse recovery time           | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7 |       | -   | 40   | -    | ns   |
|                 |                                 | $I_F = 0.5 \text{ A}; I_{rr} = 0.25 \text{ A}; I_R = 1 \text{ A}; T_j = 25 \text{ °C}$                             |       | -   | 42   | -    | ns   |
|                 |                                 | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$   |       | -   | 75   | -    | ns   |
|                 |                                 | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$  |       | -   | 130  | -    | ns   |
| I <sub>RM</sub> | peak reverse recovery current   | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 7$   |       | -   | 11.5 | -    | А    |
|                 |                                 | $I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$<br>$T_j = 125 \text{ °C}; Fig. 7$  |       | -   | 25   | -    | А    |
| E <sub>as</sub> | non-repetitive avalanche energy | T <sub>j(init)</sub> = 25 °C   |       | 45  | -    | -    | mJ   |



 $V_o$  = 1.274 V;  $R_s$  = 0.0067  $\Omega$ 

(1)  $T_j = 150$  °C; typical values (2)  $T_j = 150$  °C; maximum values (3)  $T_j = 25$  °C; maximum values



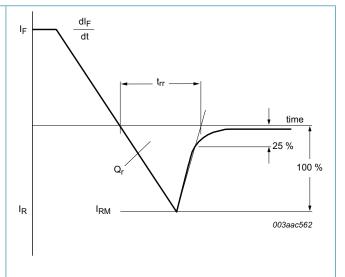
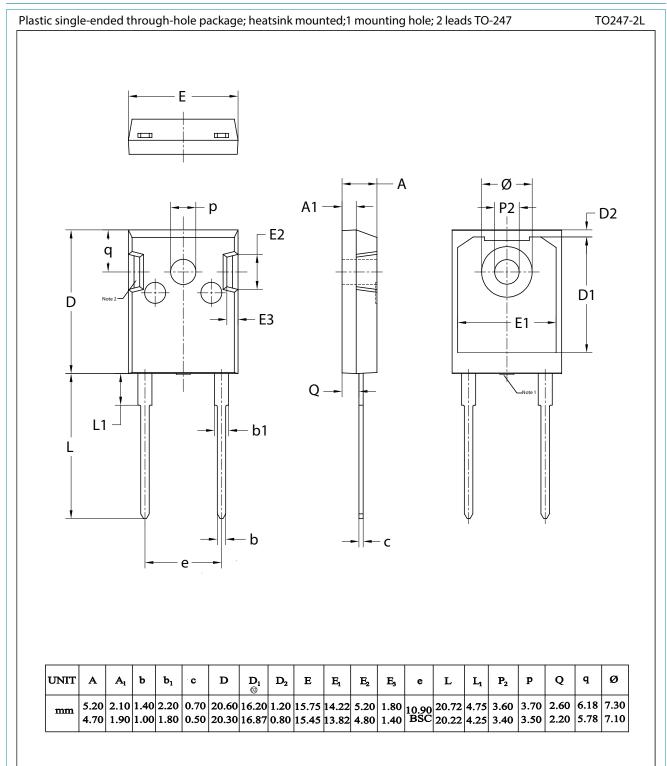


Fig. 7. Reverse recovery definitions; ramp recovery

## 11. Package outline



### Note:

- 1. Mold resin protrusion max 0.127mm.
- 2. Metal exposed with Sn plating.

### 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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